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Simon Deleonibus retired from CEA-LETI on January 1, 2016, as chief scientist after 30 years of research on the architecture of micro- and nanoelectronic devices. Before joining CEA-LETI, he was with Thomson Semiconductors (1981–1986), where he developed and transferred to production advanced microelectronic devices and products. He obtained his PhD in applied physics from Paris University (1982). A recipient of several awards and honors, he is a visiting professor at Tokyo Institute of Technology (Tokyo, Japan) since 2014, National Chiao Tung University (Hsinchu, Taiwan) since 2015, and Chinese Academy of Science (Beijing, PRC) since 2016.

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